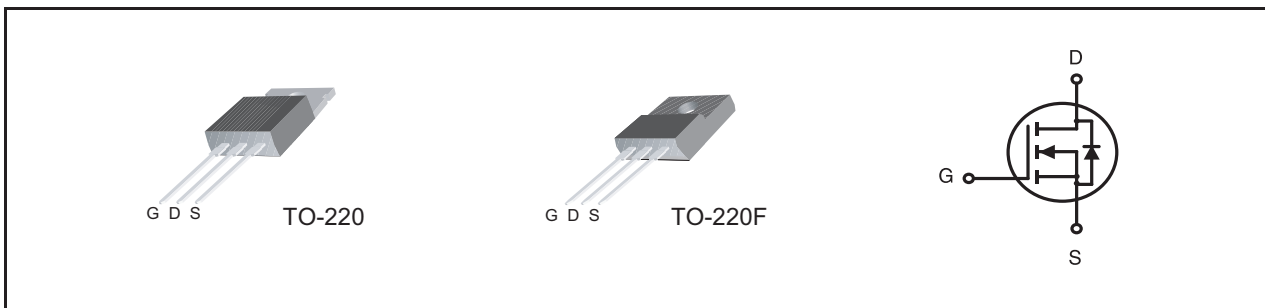


**500V N-Channel Planar MOSFET****PRODUCT SUMMARY**

| V <sub>DSS</sub> | I <sub>D</sub> | R <sub>DS(ON)</sub> (mΩ) Max                      |
|------------------|----------------|---|
| 500V             | 4.5A           | 1.5 @ V <sub>GS</sub> =10V, I <sub>D</sub> =2.25A |

**FEATURES**

- Fast Switching.
- 100% Avalanche Rated.

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

| Symbol                            | Parameter   | SDP830                | SDF830 | Units |      |
|-----------------------------------|---|-----------------------|--------|-------|------|
| V <sub>DSS</sub>                  | Drain-Source Voltage                                    | 500                   |        | V     |      |
| V <sub>GS</sub>                   | Gate-Source Voltage                                     | ±30                   |        | V     |      |
| I <sub>D</sub>                    | Continuous Drain Current                                | T <sub>C</sub> =25°C  | 4.5    | 4.5 * | A    |
|                                   |   | T <sub>C</sub> =100°C | 2.7    | 2.7 * | A    |
| I <sub>DM</sub>                   | Pulsed Drain Current, V <sub>GS</sub> =10V <sup>a</sup> | 18                    | 18 *   | A     |      |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy <sup>b</sup>              | 230                   |        | mJ    |      |
| dv/dt                             | Peak Diode Recovery Energy <sup>c</sup>                 | 4.5                   |        | V/ns  |      |
| P <sub>D</sub>                    | Power Dissipation                                       | T <sub>C</sub> =25°C  | 69     | 28    | W    |
|                                   | Linear Derating Factor                                  | T <sub>C</sub> >25°C  | 0.56   | 0.22  | W/°C |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                 | -55 to 150            |        | °C    |      |

\* Drain current limited by maximum junction temperature

**THERMAL CHARACTERISTICS**

| Symbol            | Parameter                               | SDP830 | SDF830 | Units |
|-------------------|---|--------|--------|-------|
| R <sub>θ JC</sub> | Thermal Resistance, Junction-to-Case    | 1.8    | 4.5    | °C/W  |
| R <sub>θ JA</sub> | Thermal Resistance, Junction-to-Ambient | 62.5   | 62.5   | °C/W  |

# SDP/F830

Preliminary

## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

| Symbol  | Parameter                                     | Conditions   | Min | Typ | Max  | Units |
|---|---|--|-----|-----|------|-------|
| <b>OFF CHARACTERISTICS</b>  |   |  |     |     |      |       |
| V <sub>(BR)DSS</sub>  | Drain-Source Breakdown Voltage                | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA   | 500 |     |      | V     |
| ΔV <sub>(BR)DSS</sub> / ΔT <sub>J</sub>   | Breakdown Voltage Temperature Coefficient     | Reference to 25°C, I <sub>D</sub> =250uA   |     | 0.6 |      | V/°C  |
| I <sub>DSS</sub>  | Drain-to-Source Leakage Current               | V <sub>DS</sub> =500V, V <sub>GS</sub> =0V   |     |     | 20   | uA    |
| I <sub>GSSF</sub>   | Gate-Body Leakage Current, Forward            | V <sub>DS</sub> =0V, V <sub>GS</sub> =30V  |     |     | 100  | nA    |
| I <sub>GSSR</sub>   | Gate-Body Leakage Current, Reverse            | V <sub>DS</sub> =0V, V <sub>GS</sub> =-30V   |     |     | -100 | nA    |
| <b>ON CHARACTERISTICS</b>   |   |  |     |     |      |       |
| V <sub>GS(th)</sub>   | Gate Threshold Voltage                        | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA   | 2.0 |     | 4.0  | V     |
| R <sub>DS(ON)</sub>   | Static Drain-Source On-Resistance             | V <sub>GS</sub> =10V, I <sub>D</sub> =2.25A <sup>d</sup>   |     |     | 1.5  | ohm   |
| g <sub>FS</sub>   | Forward Transconductance                      | V <sub>DS</sub> =15V, I <sub>D</sub> =2.25A <sup>d</sup>   |     |     | 10   | S     |
| <b>DYNAMIC CHARACTERISTICS</b>  |   |  |     |     |      |       |
| C <sub>ISS</sub>  | Input Capacitance                             | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V<br>f=1.0MHz  |     | 490 |      | pF    |
| C <sub>OSS</sub>  | Output Capacitance                            |  |     | 66  |      | pF    |
| C <sub>RSS</sub>  | Reverse Transfer Capacitance                  |  |     | 5   |      | pF    |
| <b>SWITCHING CHARACTERISTICS</b>  |   |  |     |     |      |       |
| t <sub>D(ON)</sub>  | Turn-On Delay Time                            | V <sub>DD</sub> =250V<br>I <sub>D</sub> =4.5A<br>R <sub>G</sub> =10 ohm, R <sub>D</sub> =55.6 ohm<br>V <sub>GS</sub> =10V <sup>d</sup> |     | 13  |      | ns    |
| t <sub>r</sub>  | Turn-On Rise Time                             |  |     | 22  |      | ns    |
| t <sub>D(OFF)</sub>   | Turn-Off Delay Time                           |  |     | 28  |      | ns    |
| t <sub>f</sub>  | Turn-Off Fall Time                            |  |     | 20  |      | ns    |
| Q <sub>g</sub>  | Total Gate Charge                             | V <sub>DS</sub> =250V, I <sub>D</sub> =4.5A,<br>V <sub>GS</sub> =10V <sup>d</sup>  |     | 11  |      | nC    |
| Q <sub>gs</sub>   | Gate-Source Charge                            |  |     | 3   |      | nC    |
| Q <sub>gd</sub>   | Gate-Drain("Miller") Charge                   |  |     | 5   |      | nC    |
| <b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>   |   |  |     |     |      |       |
| I <sub>S</sub>  | Maximum Continuous Source Current(Body Diode) |  |     |     | 4.5  | A     |
| I <sub>SM</sub>   | Maximum Pulsed Source Current(Body Diode)     |  |     |     | 18   | A     |
| V <sub>SD</sub>   | Drain-Source Diode Forward Voltage            | V <sub>GS</sub> =0V, I <sub>S</sub> =2.25A <sup>d</sup>  |     |     | 1.5  | V     |
| <b>Notes :</b>  |   |  |     |     |      |       |
| a. Repetitive Rating : Pulse width limited by maximum junction temperature.                                 |   |  |     |     |      |       |
| b. V <sub>DD</sub> =50V, starting T <sub>J</sub> =25°C, L=23mH, R <sub>G</sub> =25Ω, I <sub>AS</sub> =4.5A  |   |  |     |     |      |       |
| c. I <sub>SD</sub> ≤ 4.5A, di/dt ≤ 100A/us, V <sub>DD</sub> ≤ V <sub>(BR)DSS</sub> , T <sub>J</sub> ≤ 150°C |   |  |     |     |      |       |
| d. Pulse Test : Pulse width ≤ 300us, Duty cycle ≤ 2%.   |   |  |     |     |      |       |

Jul,22,2009

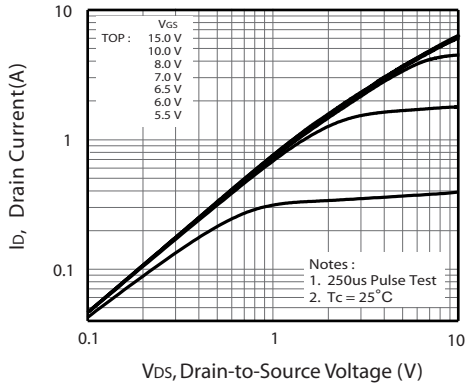


Figure 1. Output Characteristics

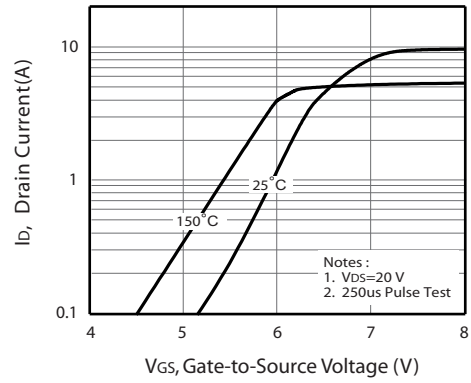


Figure 2. Transfer Characteristics

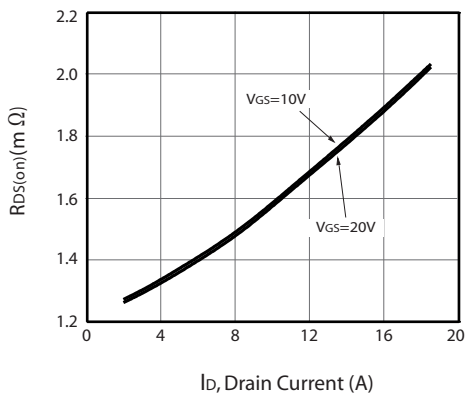
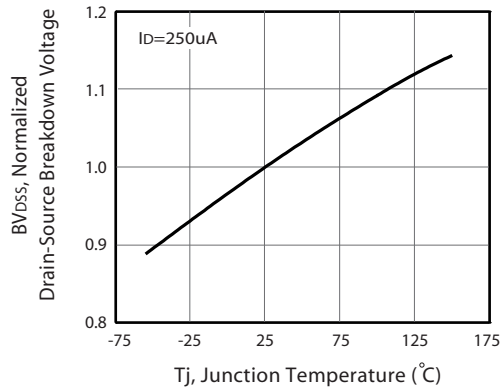


Figure 3. On-Resistance vs. Drain Current and Gate Voltage



with Temperature

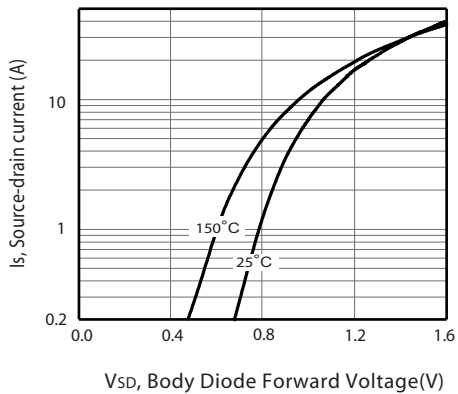


Figure 5. Body Diode Forward Voltage Variation with Source Current

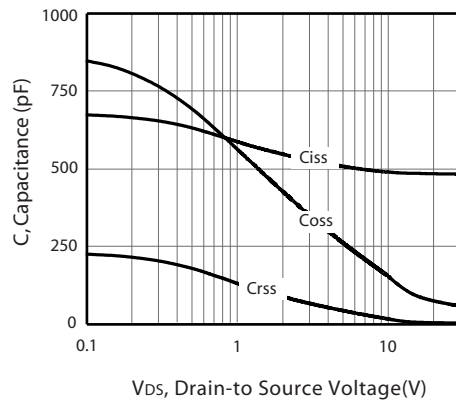
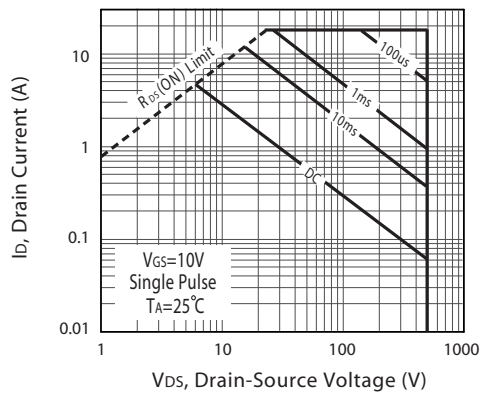
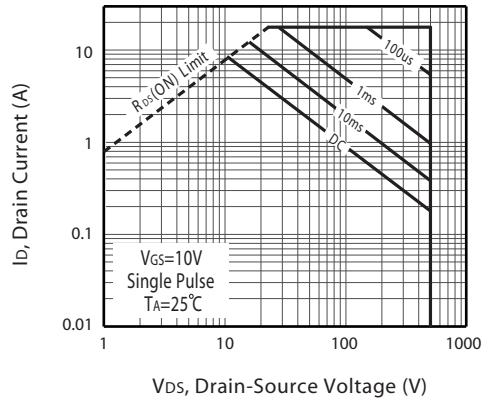
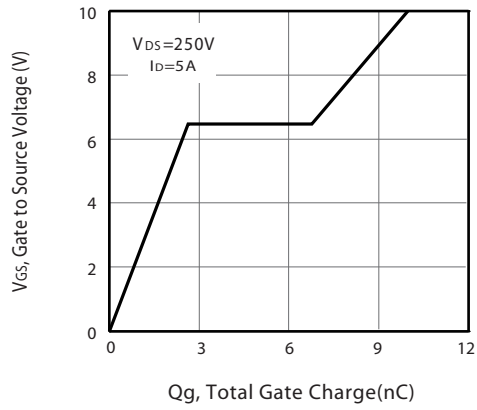
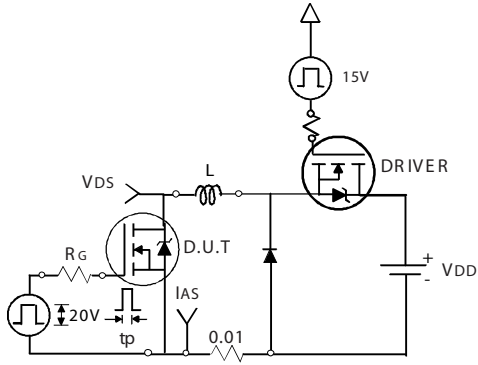


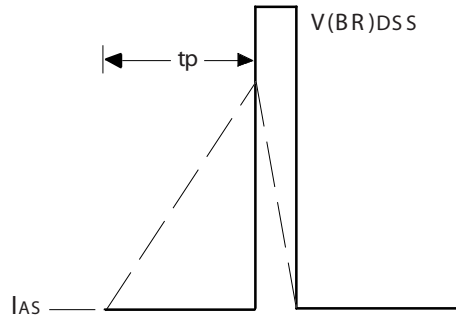
Figure 6. Capacitance





Unclamped Inductive Test Circuit

Figure 9a.



Unclamped Inductive Waveforms

Figure 9b.

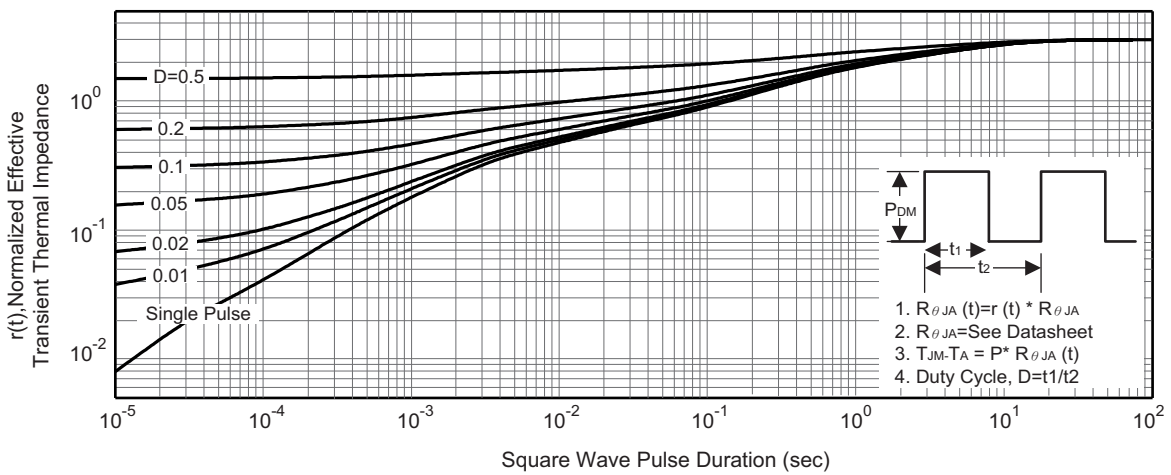


Figure 10. Normalized Thermal Transient Impedance Curve for SDP830

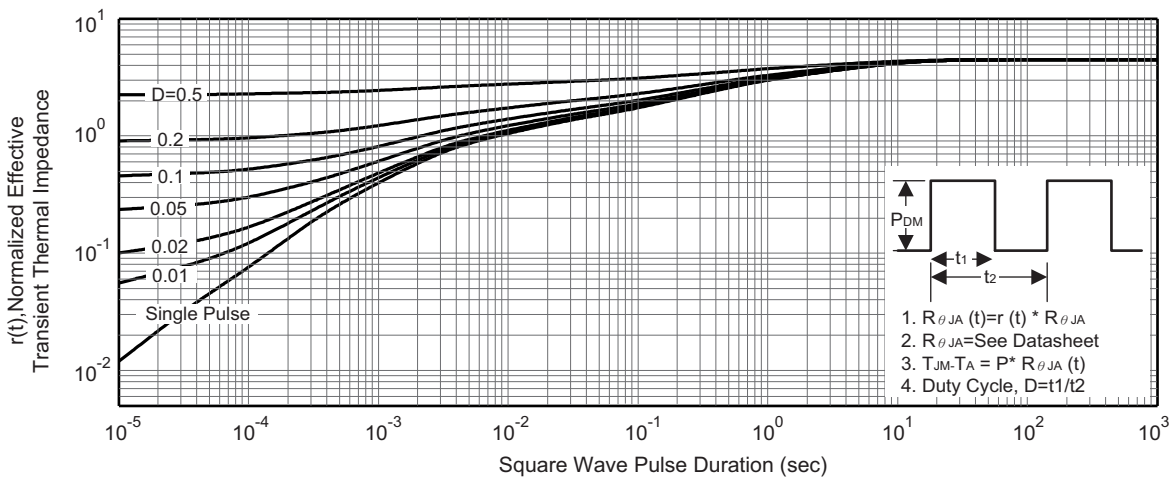
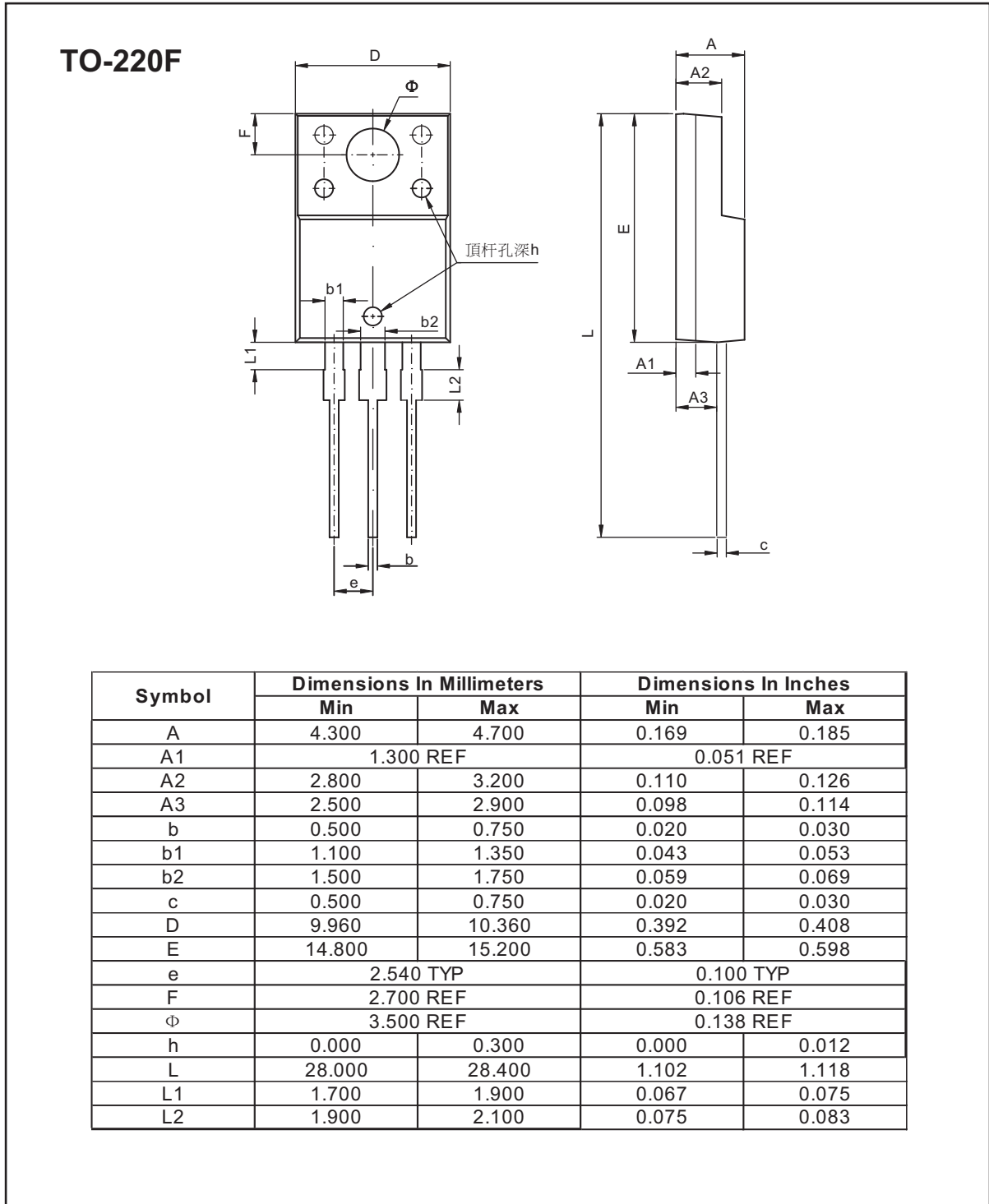


Figure 10. Normalized Thermal Transient Impedance Curve for SDF830



PACKAGE OUTLINE DIMENSIONS



## TO-220/220F Tube

